

### **isc** Silicon PNP Transistor

# **PMBT3906**

#### **DESCRIPTION**

- PNP switching transistor in a SOT23 plastic package
- NPN complement:PMBT3904
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

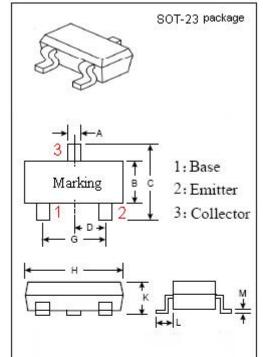


### **APPLICATIONS**

Designed for telephony and professional communication equipment

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	-40	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	-40	V	
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V	
Ic	Collector Current-Continuous	-100	mA	
Ісм	Peak Collector Current	-200	mA	
Pc	Collector Power Dissipation @Tc= 75℃	0.25	W	
TJ	Junction Temperature -65~150		$^{\circ}$ C	
T <sub>stg</sub>	Storage Temperature Range	-65~150	${\mathbb C}$	



nesson e	mm		
DIM	MIN	MAX	
A	0.30	0.50	
В	1.20	1.40	
С	2.25	2.55	
D	0.9	95	
G	1.80	3.00	
Н	2.80	3.05	
K	0.90	1.15	
L	0	.55	
M	0.08	0.15	



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### **ELECTRICAL CHARACTERISTICS**

 $T_{\text{C}}$ =25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT				
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-100	nA				
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -40V; I <sub>E</sub> = 0			-100	nA				
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -10mA ; V <sub>CE</sub> =-1 V	100		300					
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -50mA ; V <sub>CE</sub> =-1 V	60							
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = -100mA ; V <sub>CE</sub> =-1 V	30							
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -50mA; I <sub>B</sub> = -5mA			-0.3	V				
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I <sub>C</sub> = -50mA; I <sub>B</sub> = -5mA			-0.95	V				
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = -10mA ; V <sub>CE</sub> = -20V; f= 100MHz	250			MHz				
Switching times										
td	Delay Time	I <sub>C</sub> =-10mA ;I <sub>B1</sub> =-1mA;			35	ns				
tr	Rise Time	V <sub>BE(off)</sub> =0.5V; V <sub>CC</sub> =-3V			35	ns				
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = -10mA ;I <sub>B1</sub> =-1mA; I <sub>B2</sub> = 1mA V <sub>CC</sub> = -3V			225	ns				
t <sub>f</sub>	Fall Time				75	ns				



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